

# Plastic Medium-Power Complementary Silicon Transistors

... designed for general-purpose amplifier and low-speed switching applications.

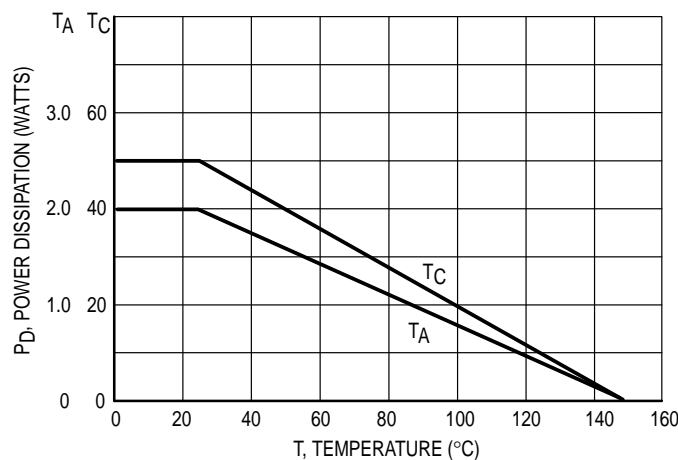
- High DC Current Gain —  
 $h_{FE} = 2500$  (Typ) @  $I_C = 1.0$  Adc
- Collector-Emitter Sustaining Voltage — @ 30 mAdc  
 $V_{CEO(sus)} = 60$  Vdc (Min) — TIP110, TIP115  
 $= 80$  Vdc (Min) — TIP111, TIP116  
 $= 100$  Vdc (Min) — TIP112, TIP117
- Low Collector-Emitter Saturation Voltage —  
 $V_{CE(sat)} = 2.5$  Vdc (Max) @  $I_C = 2.0$  Adc
- Monolithic Construction with Built-in Base-Emitter Shunt Resistors
- TO-220AB Compact Package

**\*MAXIMUM RATINGS**

Rating	Symbol	TIP110, TIP115	TIP111, TIP116	TIP112, TIP117	Unit
Collector-Emitter Voltage	$V_{CEO}$	60	80	100	Vdc
Collector-Base Voltage	$V_{CB}$	60	80	100	Vdc
Emitter-Base Voltage	$V_{EB}$	5.0			Vdc
Collector Current — Continuous Peak	$I_C$	2.0 4.0			Adc
Base Current	$I_B$	50			mAdc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	50 0.4			Watts W/ $^\circ\text{C}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	2.0 0.016			Watts W/ $^\circ\text{C}$
Unclamped Inductive Load Energy — Figure 13	E	25			mJ
Operating and Storage Junction	$T_J, T_{stg}$	-65 to +150			$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.5	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$



**Figure 1. Power Derating**

Preferred devices are Motorola recommended choices for future use and best overall value.

REV 1

**NPN**  
**TIP110**  
**TIP111\***  
**TIP112\***  
**PNP**  
**TIP115**  
**TIP116\***  
**TIP117\***

\*Motorola Preferred Device

**DARLINGTON**  
**2 AMPERE**  
**COMPLEMENTARY SILICON**  
**POWER TRANSISTORS**  
**60-80-100 VOLTS**  
**50 WATTS**

**CASE 221A-06**  
**TO-220AB**

**TIP110 TIP111 TIP112 TIP115 TIP116 TIP117**

**ELECTRICAL CHARACTERISTICS** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Sustaining Voltage (1) ( $I_C = 30\text{ mAdc}$ , $I_B = 0$ )	$V_{CE(sus)}$	60 80 100	—	Vdc
Collector Cutoff Current ( $V_{CE} = 30\text{ Vdc}$ , $I_B = 0$ ) ( $V_{CE} = 40\text{ Vdc}$ , $I_B = 0$ ) ( $V_{CE} = 50\text{ Vdc}$ , $I_B = 0$ )	$I_{CEO}$	— — —	2.0 2.0 2.0	mAdc
Collector Cutoff Current ( $V_{CB} = 60\text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = 80\text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = 100\text{ Vdc}$ , $I_E = 0$ )	$I_{CBO}$	— — —	1.0 1.0 1.0	mAdc
Emitter Cutoff Current ( $V_{BE} = 5.0\text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	—	2.0	mAdc

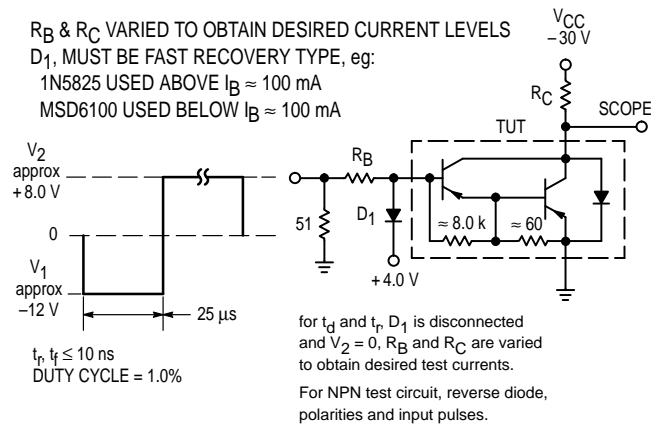
**ON CHARACTERISTICS (1)**

DC Current Gain ( $I_C = 1.0\text{ Adc}$ , $V_{CE} = 4.0\text{ Vdc}$ ) ( $I_C = 2.0\text{ Adc}$ , $V_{CE} = 4.0\text{ Vdc}$ )	$h_{FE}$	1000 500	— —	—
Collector–Emitter Saturation Voltage ( $I_C = 2.0\text{ Adc}$ , $I_B = 8.0\text{ mAdc}$ )	$V_{CE(sat)}$	—	2.5	Vdc
Base–Emitter On Voltage ( $I_C = 2.0\text{ Adc}$ , $V_{CE} = 4.0\text{ Vdc}$ )	$V_{BE(on)}$	—	2.8	Vdc

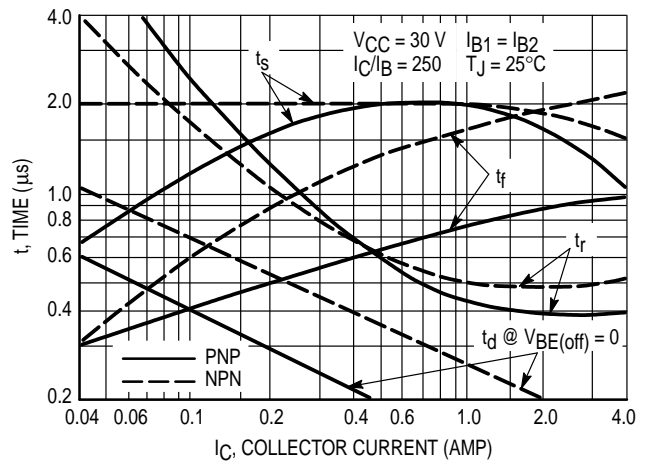
**DYNAMIC CHARACTERISTICS**

Small–Signal Current Gain ( $I_C = 0.75\text{ Adc}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ MHz}$ )	$h_{fe}$	25	—	—
Output Capacitance ( $V_{CB} = 10\text{ Vdc}$ , $I_E = 0$ , $f = 0.1\text{ MHz}$ )	$C_{ob}$	— —	200 100	pF

(1) Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .



**Figure 2. Switching Times Test Circuit**



**Figure 3. Switching Times**

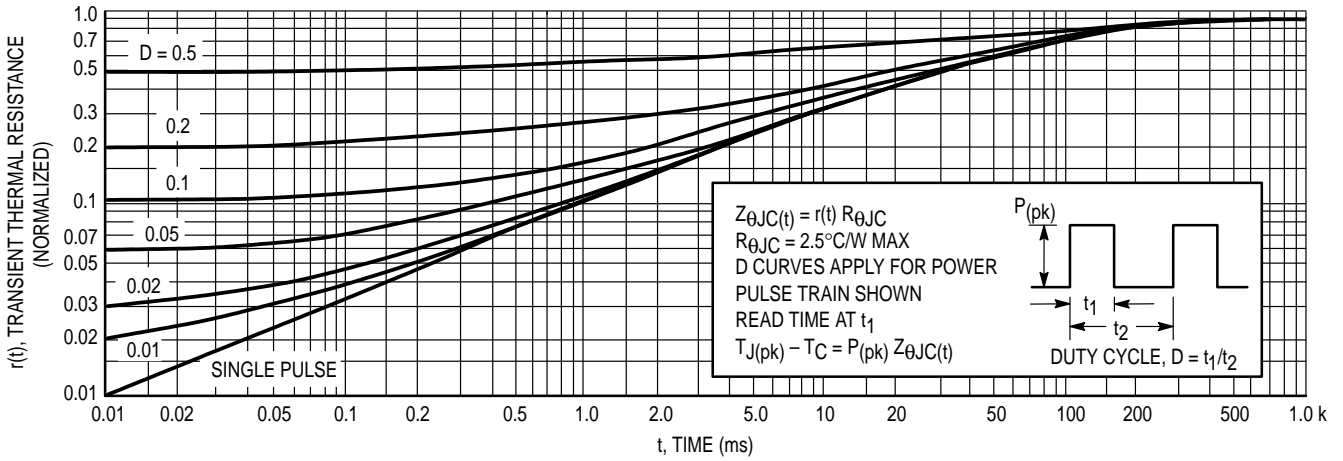


Figure 4. Thermal Response

ACTIVE-REGION SAFE-OPERATING AREA

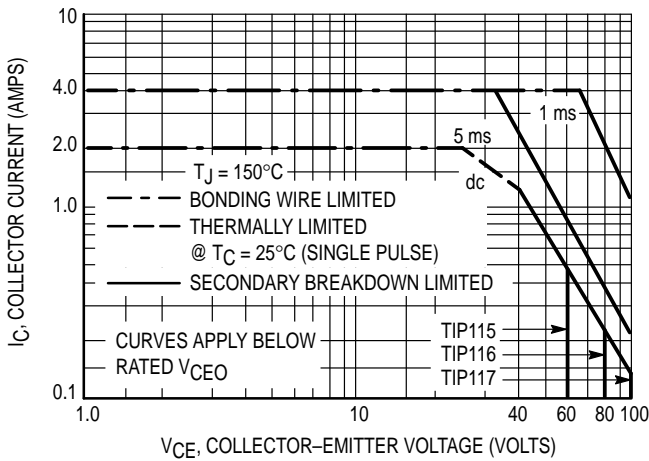


Figure 5. TIP115, 116, 117

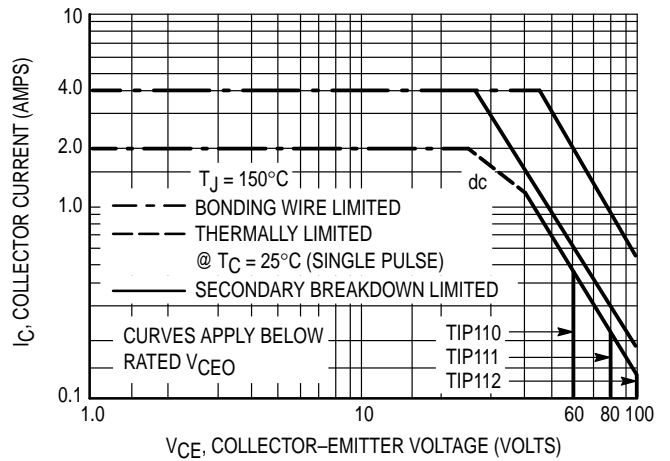


Figure 6. TIP110, 111, 112

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 5 and 6 is based on  $T_{J(pk)} = 150^{\circ}\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} < 150^{\circ}\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

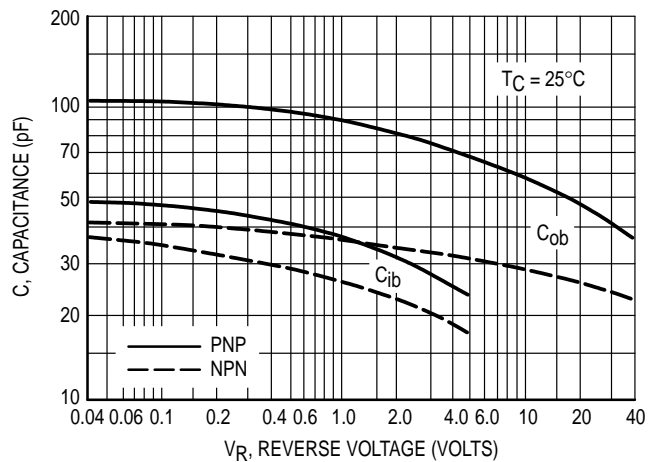


Figure 7. Capacitance

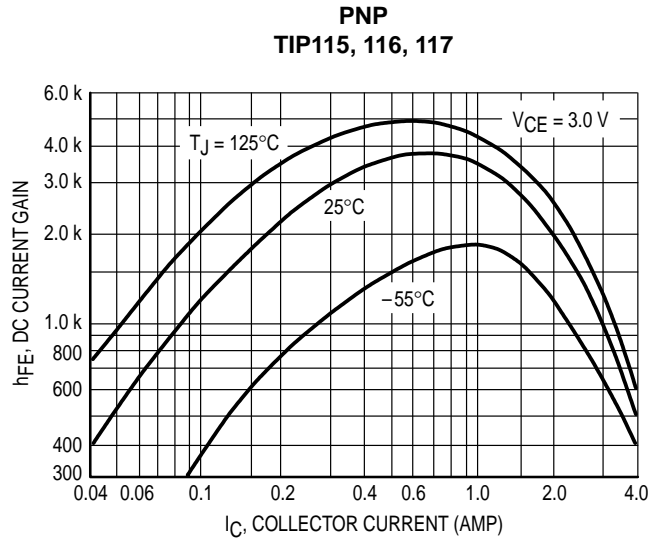
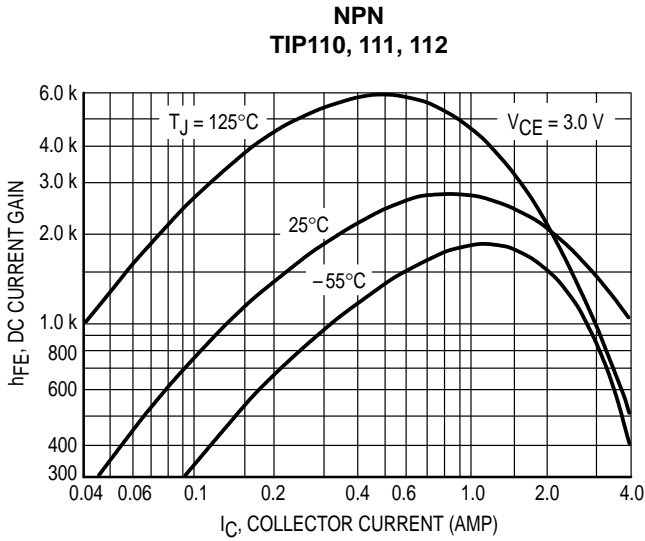


Figure 8. DC Current Gain

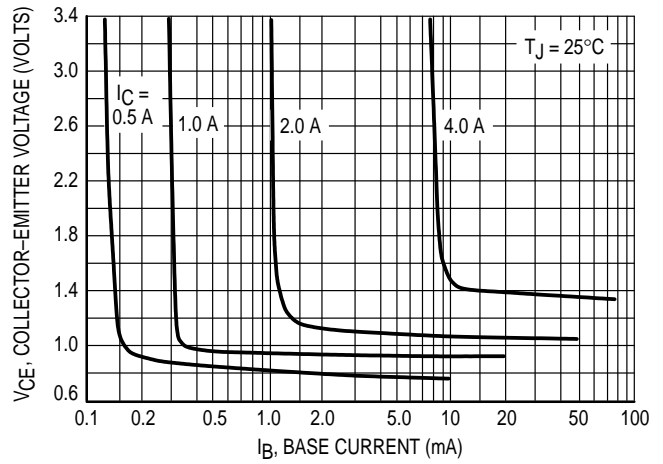
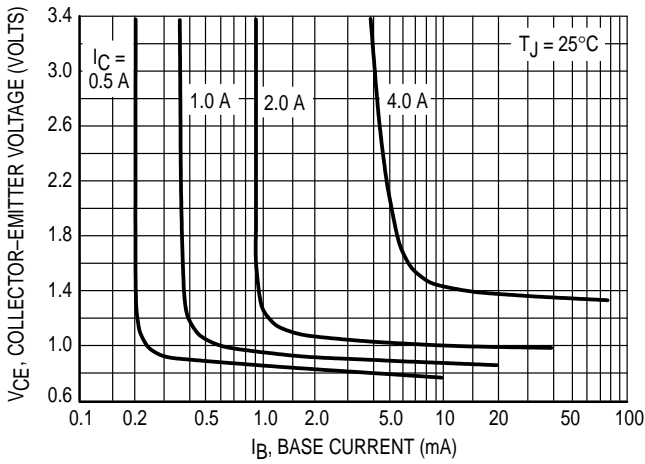


Figure 9. Collector Saturation Region

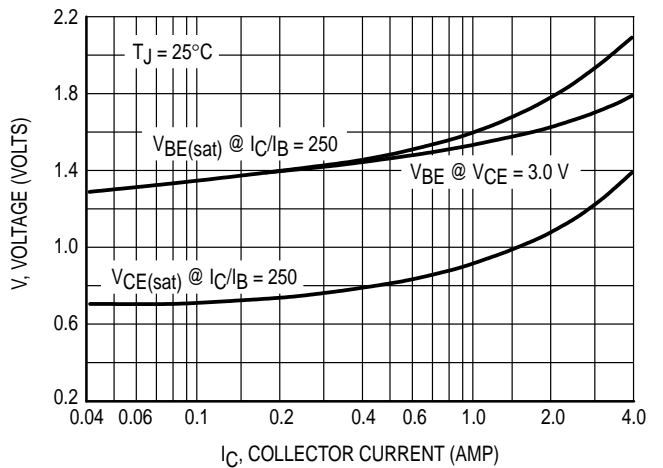
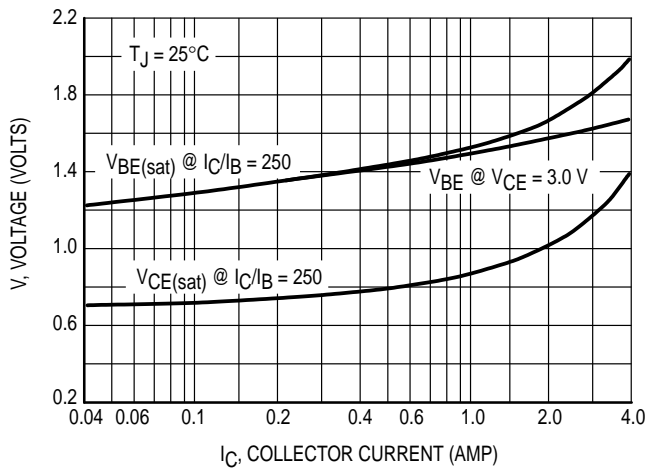


Figure 10. "On" Voltages

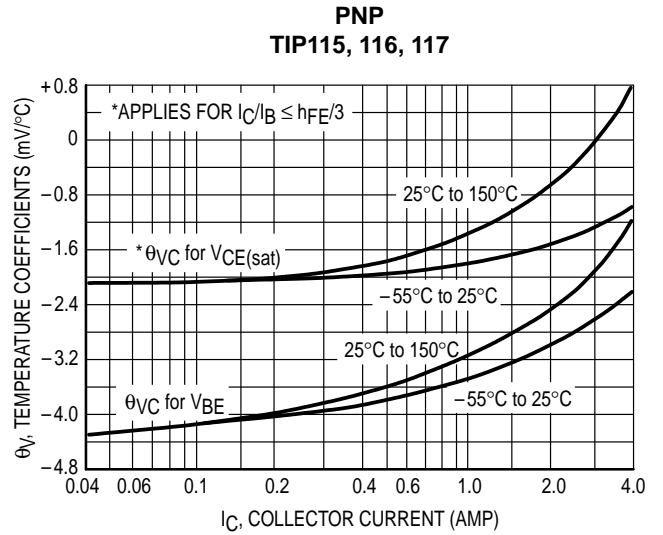
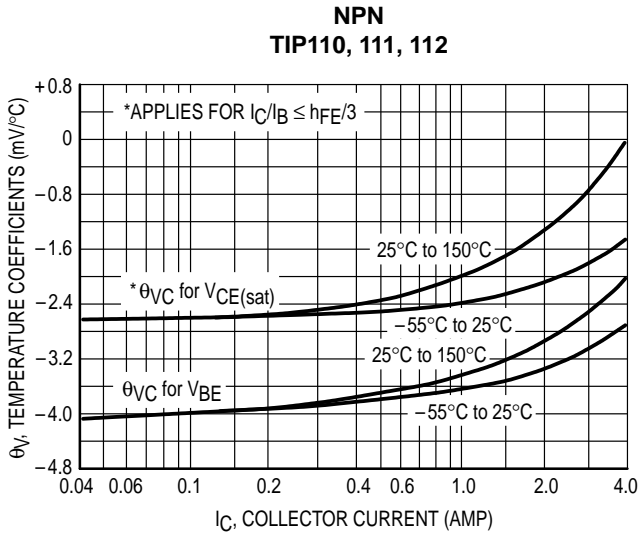


Figure 11. Temperature Coefficients

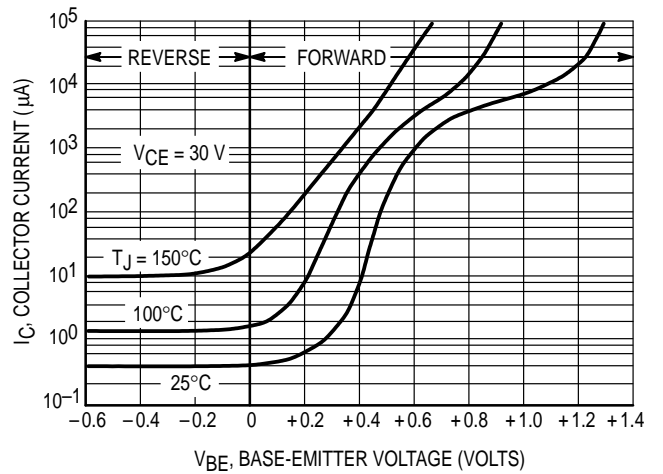
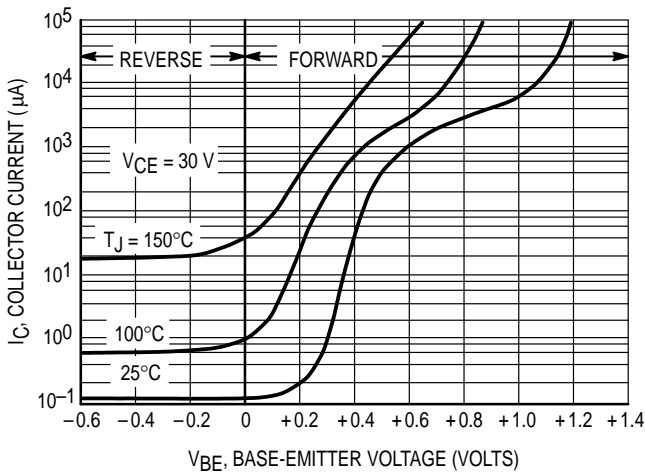
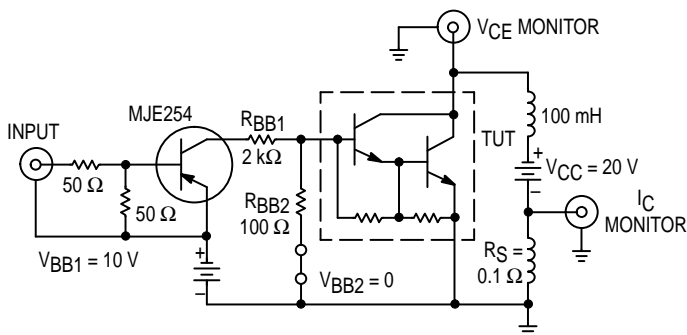


Figure 12. Collector Cut-Off Region

**TEST CIRCUIT**



Note A: Input pulse width is increased until  $I_{CM} = 0.71$  A, NPN test shown; for PNP test reverse all polarity and use MJE224 driver.

**VOLTAGE AND CURRENT WAVEFORMS**

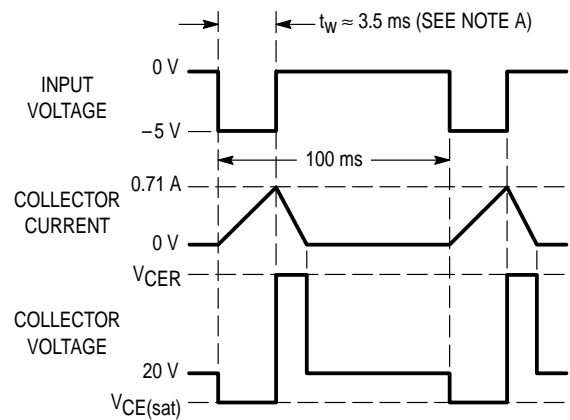
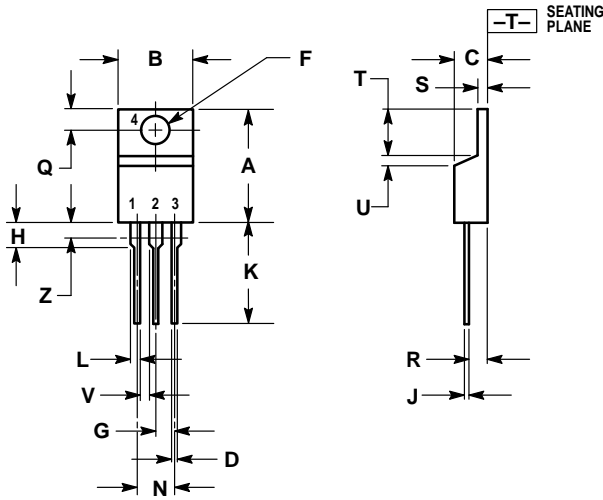


Figure 13. Inductive Load Switching

PACKAGE DIMENSIONS



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	—	1.15	—
Z	—	0.080	—	2.04

- STYLE 1:  
 PIN 1. BASE  
 2. COLLECTOR  
 3. EMITTER  
 4. COLLECTOR

CASE 221A-06  
 TO-220AB  
 ISSUE Y

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